Product data sheet

1. General description

NPN low V_{CEsat} transistor in a small SOT457 (SC-74) Surface Mounted Device (SMD) plastic package.

2. Features and benefits

- SOT457 package
- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High efficiency, leading to less heat generation
- Qualified according to AEC-Q101 and recommended for use in automotive applications

3. Applications

- Major application segments:
 - Automotive 42 V power
 - · Telecom infrastructure
 - Industrial
- DC-to-DC converter
- Peripheral driver
 - Driver in low supply voltage applications (e.g. lamps and LEDs)
 - Inductive load drivers (e.g. relays, buzzers and motors)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	100	V
I _C	collector current		-	-	1	Α
I _{CM}	peak collector current		-	-	3	Α
R _{CEsat}	collector-emitter saturation resistance	I_C = 1 A; I_B = 100 mA; $t_p \le 300 \mu s$; $δ = 0.02$	-	160	200	mΩ



100 V, 1 A NPN low VCEsat transistor

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	С	collector		
2	С	collector	<u> </u>	c
3	В	base		В
4	E	emitter	□ □ □ □ □ □ □ □ □ □ □ □ □ □ □ □ □ □ □ □) E
5	С	collector	TSOP6 (SOT457)	⊆ sym014
6	С	collector		·

6. Marking

Table 3. Marking codes

Type number	Marking code
PBSS8110D-Q	A8

7. Limiting values

Table 4. Limiting values

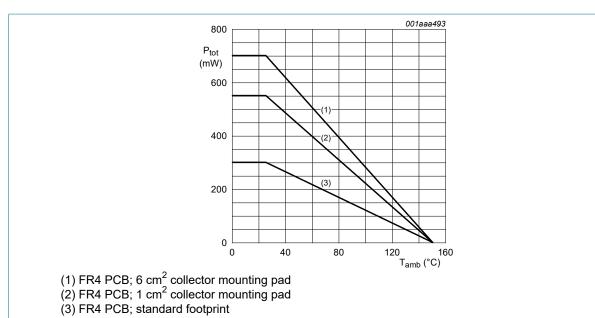
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter		-	120	V
V _{CEO}	collector-emitter voltage	open base		-	100	V
V_{EBO}	emitter-base voltage	open collector		-	5	V
I _C	collector current			-	1	Α
I _{CM}	peak collector current			-	3	Α
I _B	base current			-	0.3	Α
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	300	mW
			[2]	-	550	mW
			[3]	-	700	mW
T _j	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².

 Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

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Power derating curves Fig. 1.

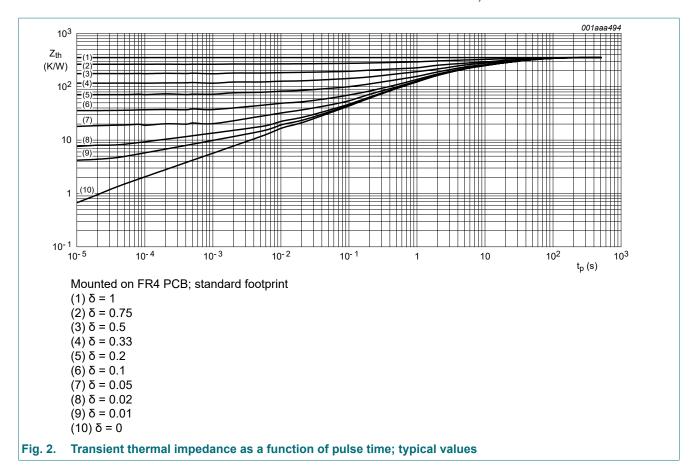
8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
α (<u>(</u> -α)	thermal resistance from	in free air	[1]	-	-	416	K/W
	junction to ambient		[2]	-	-	227	K/W
			[3]	-	-	178	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point		[4]	-	-	83	K/W

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm². Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- Device mounted on a FR4 printed-circuit board, single-sided copper, tin-plated, standard footprint.

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9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V _{CB} = 80 V; I _E = 0 A; T _{amb} = 25 °C	-	-	100	nA
	current	V _{CB} = 80 V; I _E = 0 A; T _j = 150 °C	-	-	50	μΑ
I _{CES}	collector-emitter cut-off current	V _{CE} = 80 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	100	nA
I _{EBO}	emitter-base cut-off current	V _{EB} = 4 V; I _C = 0 A; T _{amb} = 25 °C	-	-	100	nA
h _{FE}	DC current gain	V _{CE} = 10 V; I _C = 1 mA; T _{amb} = 25 °C	150	-	-	
		V _{CE} = 10 V; I _C = 250 mA; T _{amb} = 25 °C	150	-	500	
		V_{CE} = 10 V; I_{C} = 0.5 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	100	-	-	
		V_{CE} = 10 V; I_{C} = 1 A; pulsed; $t_{p} \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	80	-	-	
V _{CEsat}	collector-emitter	I_C = 100 mA; I_B = 10 mA; T_{amb} = 25 °C	-	-	40	mV
	saturation voltage	I_C = 500 mA; I_B = 50 mA; T_{amb} = 25 °C	-	-	120	mV
		I _C = 1 A; I _B = 100 mA; T _{amb} = 25 °C	-	-	200	mV
R _{CEsat}	collector-emitter saturation resistance	I_C = 1 A; I_B = 100 mA; $t_p \le 300 \mu s$; δ = 0.02	-	160	200	mΩ
V _{BEsat}	base-emitter saturation voltage	$I_C = 1 \text{ A}; I_B = 100 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$	-	-	1.05	V

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{BEon}	base-emitter turn-on voltage	V _{CE} = 10 V; I _C = 1 A; T _{amb} = 25 °C	-	-	0.9	V
f _T		V_{CE} = 10 V; I_{C} = 50 mA; f = 100 MHz; T_{amb} = 25 °C	100	-	-	MHz
C _c	collector capacitance	V_{CB} = 10 V; I_{E} = 0 A; i_{e} = 0 A; f = 1 MHz; T_{amb} = 25 °C	-	-	7.5	pF

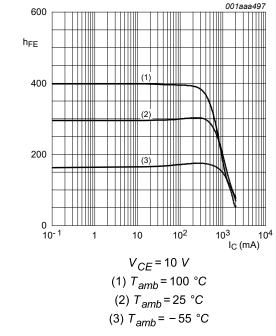
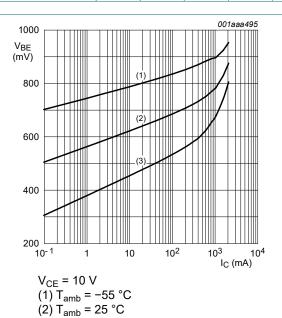
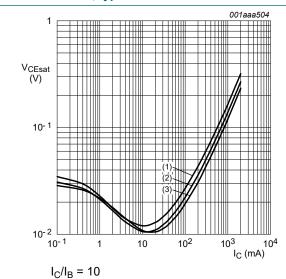


Fig. 3. DC current gain as a function of collector current; typical values



(3) T_{amb} = 100 °C Fig. 4. Base-emitter voltage as a function of collector current; typical values



(2) T_{amb} = 25 °C (3) T_{amb} = -55 °C Fig. 5. Collector-emitter saturation voltage as a function of collector current; typical values

(1) $T_{amb} = 100 \, ^{\circ}C$

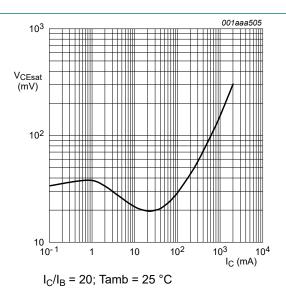


Fig. 6. Collector-emitter saturation voltage as a function of collector current; typical values

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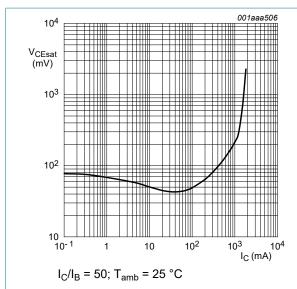
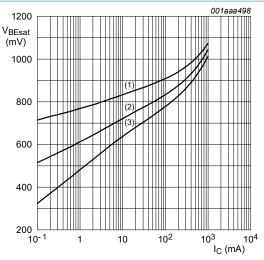


Fig. 7. Collector-emitter saturation voltage as a function of collector current; typical values



 $I_{C}/I_{B} = 10$ (1) $T_{amb} = -55 \,^{\circ}C$ (2) $T_{amb} = 25 \,^{\circ}C$ (3) $T_{amb} = 100 \,^{\circ}C$

Fig. 8. Base-emitter saturation voltage as a function of collector current; typical values

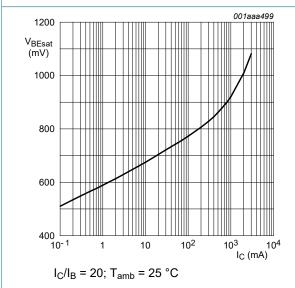
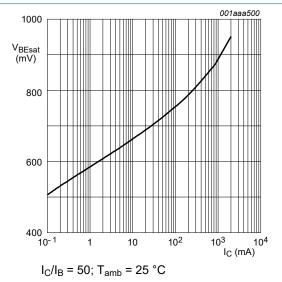


Fig. 9. collector current; typical values



Base-emitter saturation voltage as a function of Fig. 10. Base-emitter saturation voltage as a function of collector current; typical values

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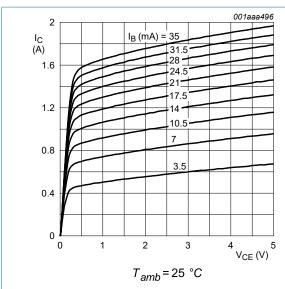


Fig. 11. Collector current as a function of collectoremitter voltage; typical values

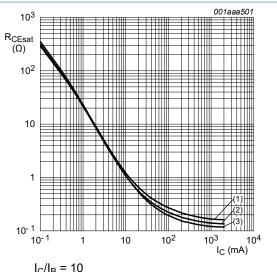


Fig. 12. Collector-emitter saturation resistance as a function of collector current; typical values

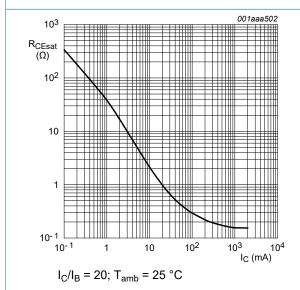


Fig. 13. Equivalent on-resistance as a function of collector current; typical values

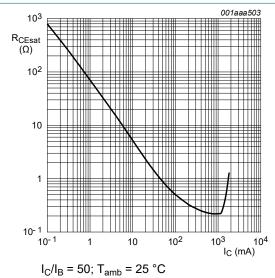
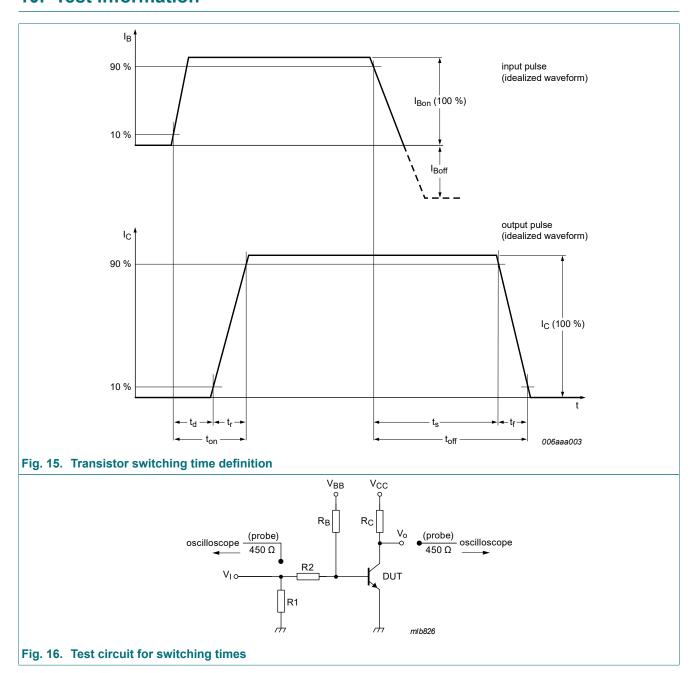


Fig. 14. Equivalent on-resistance as a function of collector current; typical values

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10. Test information

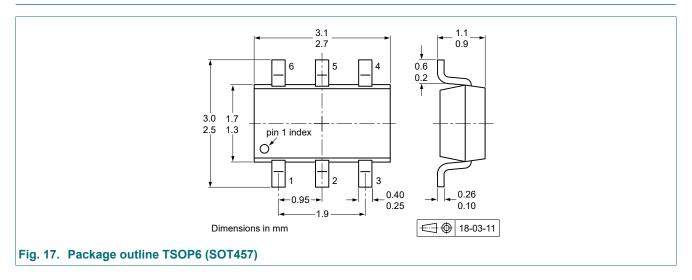


Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

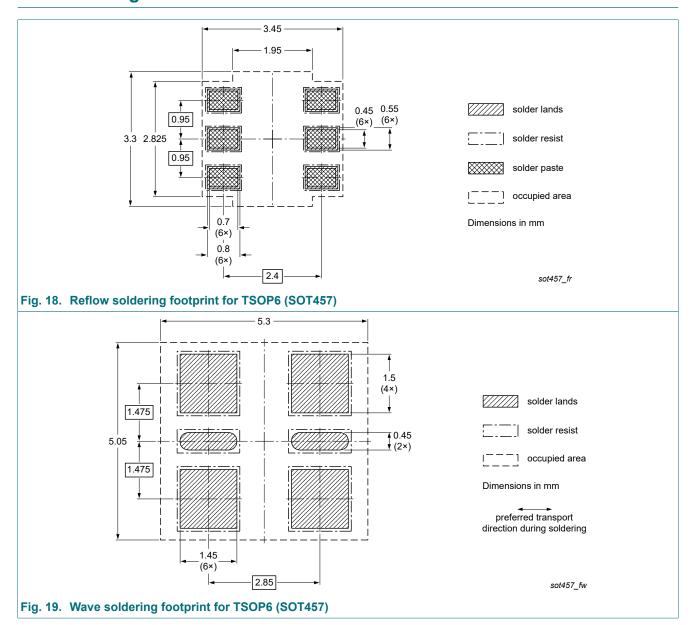
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11. Package outline



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12. Soldering



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13. Revision history

Table 7. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBSS8110D-Q v.1	20250704	Product data sheet	-	-

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14. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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